# PMEG6030ETP

High-temperature 60 V, 3 A Schottky barrier rectifier 15 October 2012 **Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features and benefits

- Average forward current:  $I_{F(AV)} \le 3 A$
- Reverse voltage: V<sub>R</sub> ≤ 60 V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T<sub>i</sub> ≤ 175 °C

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

#### 1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F</sub>	forward current	T <sub>sp</sub> = 160 °C		-	-	4.2	Α
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{amb} \le 80$ °C; square wave	[1]	-	-	3	А
		$\delta$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave		-	-	3	А
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C		-	460	530	mV
I <sub>R</sub>	reverse current	$T_j$ = 25 °C; $V_R$ = 60 V; $t_p \le$ 300 µs; $\delta \le$ 0.02 ; pulsed		-	80	200	μA





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$	-	12	-	ns
		T <sub>j</sub> = 25 °C				

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	, r	1 <del>][-]</del> 2
2	Α	anode	SOD128	sym001

[1] The marking bar indicates the cathode.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG6030ETP	SOD128	plastic surface-mounted package; 2 leads	SOD128

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6030ETP	DA

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C		-	60	V
I <sub>F</sub>	forward current	T <sub>sp</sub> = 160 °C		-	4.2	Α
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{amb} \le 80$ °C; square wave	[1]	-	3	A
		$\delta$ = 0.5 ; f = 20 kHz; T <sub>sp</sub> ≤ 165 °C; square wave		-	3	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	750	mW
			[3]	-	1250	mW
			[1]	-	2500	mW
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

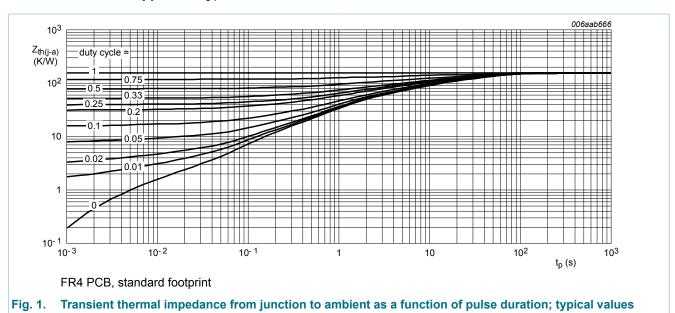
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	200	K/W
from junction to ambient		[1][3]	-	-	120	K/W	
	ambient	[1	[1][4]	-	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	12	K/W

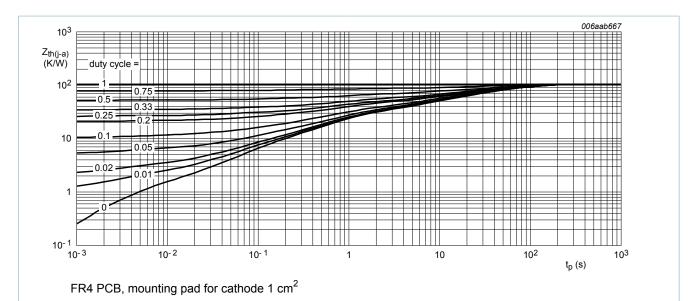
- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.



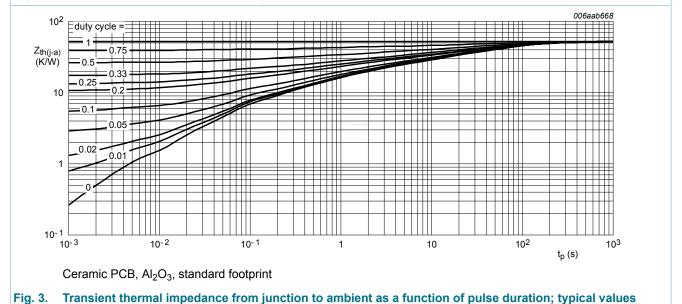
PMEG6030ETP

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### High-temperature 60 V, 3 A Schottky barrier rectifier



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.



#### **7**. **Characteristics**

**Characteristics** Table 7.

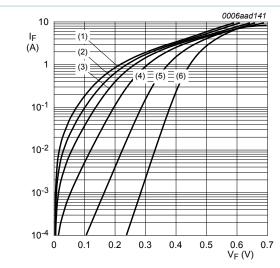
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub> forward voltage		I <sub>F</sub> = 0.1 A; T <sub>j</sub> = 25 °C	-	290	330	mV
	I <sub>F</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	340	400	mV	
	I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C	-	380	440	mV	
		I <sub>F</sub> = 1.5 A; T <sub>j</sub> = 25 °C	-	400	470	mV
		I <sub>F</sub> = 2 A; T <sub>j</sub> = 25 °C	-	430	500	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C	-	460	530	mV

### High-temperature 60 V, 3 A Schottky barrier rectifier

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
		I <sub>F</sub> = 3 A; T <sub>j</sub> = -40 °C	-	510	590	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 125 °C	-	405	480	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 150 °C	-	390	460	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 175 °C	-	370	450	mV
I <sub>R</sub>	reverse current	$V_R$ = 5 V; $T_j$ = 25 °C; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; pulsed	-	4	-	μA
		$V_R$ = 10 V; $T_j$ = 25 °C; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; pulsed	-	5	-	μA
		$V_R$ = 60 V; $T_j$ = 25 °C; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; pulsed	-	80	200	μA
		$V_R$ = 60 V; $T_j$ = -40 °C; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; pulsed	-	0.5	10	μA
		$V_R$ = 60 V; $T_j$ = 125 °C; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02 ; pulsed	-	45	150	mA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	360	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	120	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}$ ; $I_R = 0.5 \text{ A}$ ; $I_{R(meas)} = 0.1 \text{ A}$ ; $I_{j} = 25 \text{ °C}$	-	12	-	ns
V <sub>FRM</sub>	peak forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 40 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	425	-	mV

#### High-temperature 60 V, 3 A Schottky barrier rectifier



(1) 
$$T_i = 175 \,^{\circ}C$$

(2) 
$$T_i = 150 \, ^{\circ}C$$

(3) 
$$T_i = 125 \, ^{\circ}C$$

(4) 
$$T_i = 85 \, ^{\circ}C$$

(5) 
$$T_i = 25 \, ^{\circ}C$$

(6) 
$$T_i = -40 \, ^{\circ}C$$

Fig. 4. Forward current as a function of forward voltage; typical values

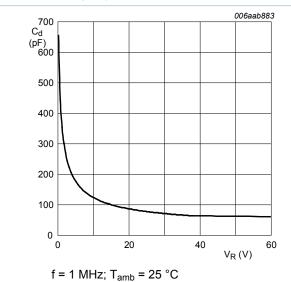
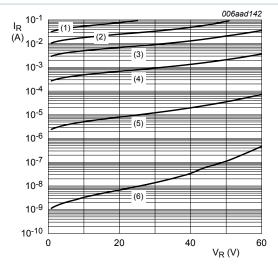


Fig. 6. Diode capacitance as a function of reverse

voltage; typical values



(1) 
$$T_i = 175 \, ^{\circ}C$$

(2) 
$$T_j = 150 \, ^{\circ}\text{C}$$

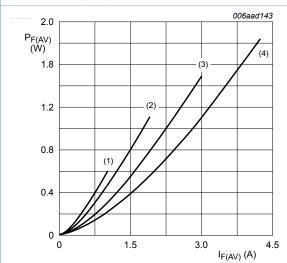
(3) 
$$T_i = 125 \,^{\circ}C$$

(4) 
$$T_i = 85 \, ^{\circ}C$$

(5) 
$$T_i = 25 \, ^{\circ}C$$

(6) 
$$T_i = -40 \,^{\circ}\text{C}$$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$$(1) \delta = 0.1$$

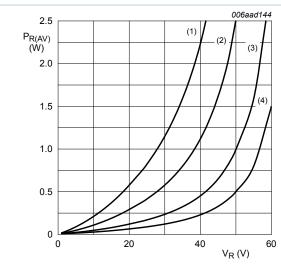
(2) 
$$\delta = 0.2$$

$$(3) \delta = 0.5$$

$$(4) \delta = 1$$

ig. 7. Average forward power dissipation as a function of average forward current; typical values

#### High-temperature 60 V, 3 A Schottky barrier rectifier

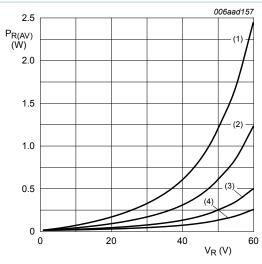


$$(2) \delta = 0.5$$

$$(3) \delta = 0.2$$

$$(4) \delta = 0.1$$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



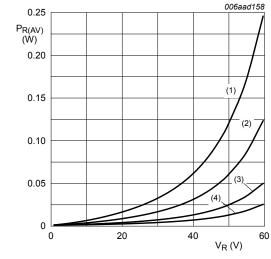
$$(1) \delta = 1$$

$$(2) \delta = 0.5$$

$$(3) \delta = 0.2$$

$$(4) \delta = 0.1$$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



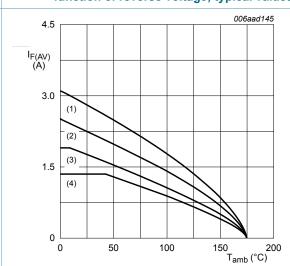
$$(1) \delta = 1$$

(2) 
$$\delta = 0.5$$

$$(3) \delta = 0.2$$

$$(4) \delta = 0.1$$

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

(1) 
$$\delta = 1$$
 (DC)

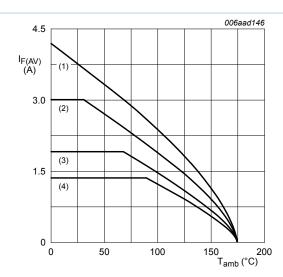
(2) 
$$\delta = 0.5$$
;  $f = 20 \text{ kHz}$ 

(3) 
$$\delta$$
 = 0.2; f = 20 kHz

(4) 
$$\delta$$
 = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values

#### High-temperature 60 V, 3 A Schottky barrier rectifier



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

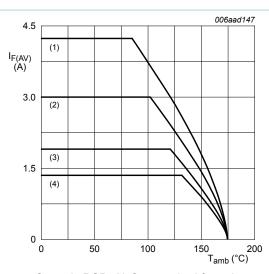
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

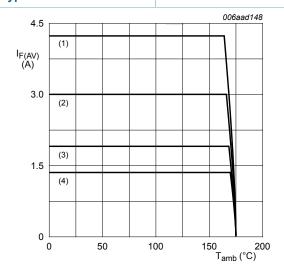
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 13. Average forward current as a function of ambient temperature; typical values



T<sub>i</sub> = 175 °C

(1)  $\delta = 1$  (DC)

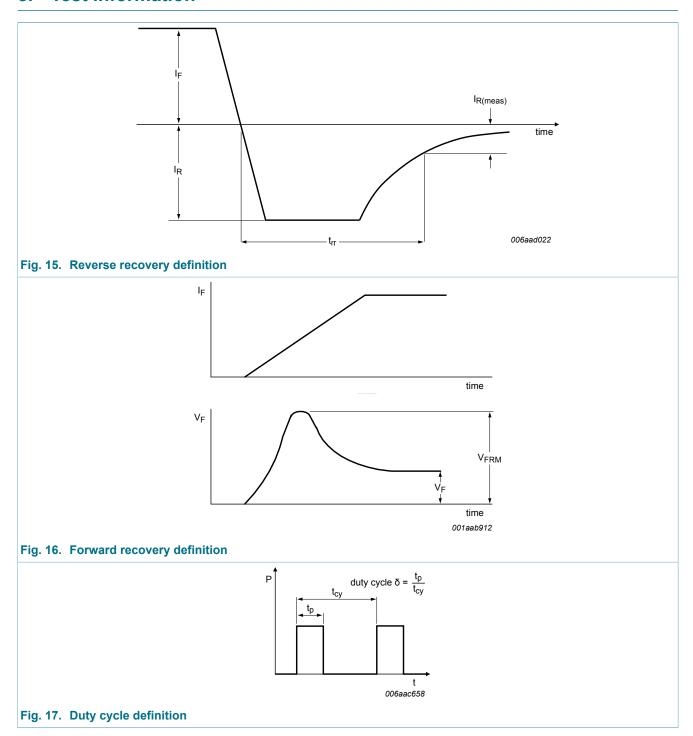
(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 14. Average forward current as a function of solder point temperature; typical values

### 8. Test information



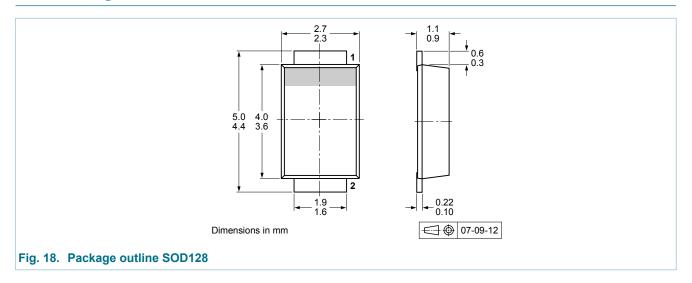
The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### High-temperature 60 V, 3 A Schottky barrier rectifier

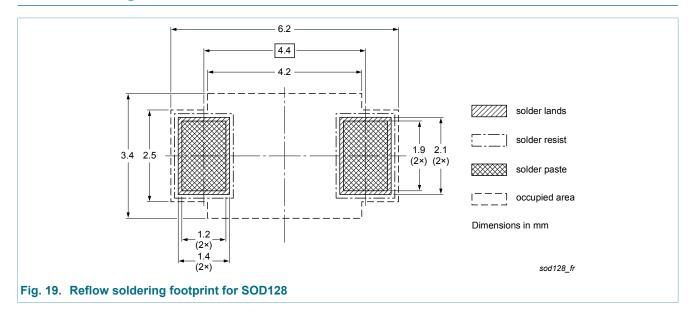
## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Soldering



# 11. PMEG6030ETP

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6030ETP v.1	20121015	Product data sheet	-	-

# 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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